

Title (en)  
CLEANING OF A PROCESS CHAMBER

Title (de)  
REINIGEN EINER PROZESSKAMMER

Title (fr)  
NETTOYAGE D'UNE CHAMBRE DE TRAITEMENT

Publication  
**EP 2459767 A1 20120606 (DE)**

Application  
**EP 10724707 A 20100528**

Priority  
• DE 102009035045 A 20090726  
• DE 102010008499 A 20100218  
• EP 2010003247 W 20100528

Abstract (en)  
[origin: WO2011012185A1] The method for cleaning at least one component arranged in the inner region of a plasma process chamber by using a cleaning gas which comprises fluorine gas, the process chamber having at least one electrode and counter-electrode for producing a plasma for the plasma treatment, in particular the CVD or PECVD treatment, of flat substrates with a surface of over 1 m<sup>2</sup>, is distinguished by the fact that the inner region is subjected to gaseous fluorine compounds with a partial pressure of greater than 5 mbar. In a further method V for cleaning at least one component arranged in the inner region of a process chamber by means of a cleaning gas which comprises fluorine gas, the process chamber having at least one electrode and counter-electrode for producing a plasma, in particular for the CVD or PECVD treatment, of flat substrates with a surface of over 1 m<sup>2</sup>, it is provided that the fluorine gas is thermally activated by means of a temperature control medium, the component to be cleaned being at a temperature of < 350° C.

IPC 8 full level  
**C23C 16/44** (2006.01); **B08B 7/00** (2006.01); **H01J 37/32** (2006.01)

CPC (source: EP KR US)  
**B08B 7/0035** (2013.01 - KR); **B08B 7/0071** (2013.01 - EP US); **C23C 16/44** (2013.01 - KR); **C23C 16/4405** (2013.01 - EP US); **H01J 37/32** (2013.01 - KR); **H01J 37/32862** (2013.01 - EP US); **H01L 21/02367** (2013.01 - KR)

Citation (search report)  
See references of WO 2011012185A1

Designated contracting state (EPC)  
AL AT BE BG CH CY CZ DE DK EE ES FI FR GB GR HR HU IE IS IT LI LT LU LV MC MK MT NL NO PL PT RO SE SI SK SM TR

DOCDB simple family (publication)  
**WO 2011012185 A1 20110203**; CN 102597306 A 20120718; EP 2459767 A1 20120606; JP 2013500595 A 20130107; KR 20120054023 A 20120529; TW 201126011 A 20110801; US 2012180810 A1 20120719

DOCDB simple family (application)  
**EP 2010003247 W 20100528**; CN 201080036325 A 20100528; EP 10724707 A 20100528; JP 2012521986 A 20100528; KR 20127004640 A 20100528; TW 99118052 A 20100604; US 201013386711 A 20100528